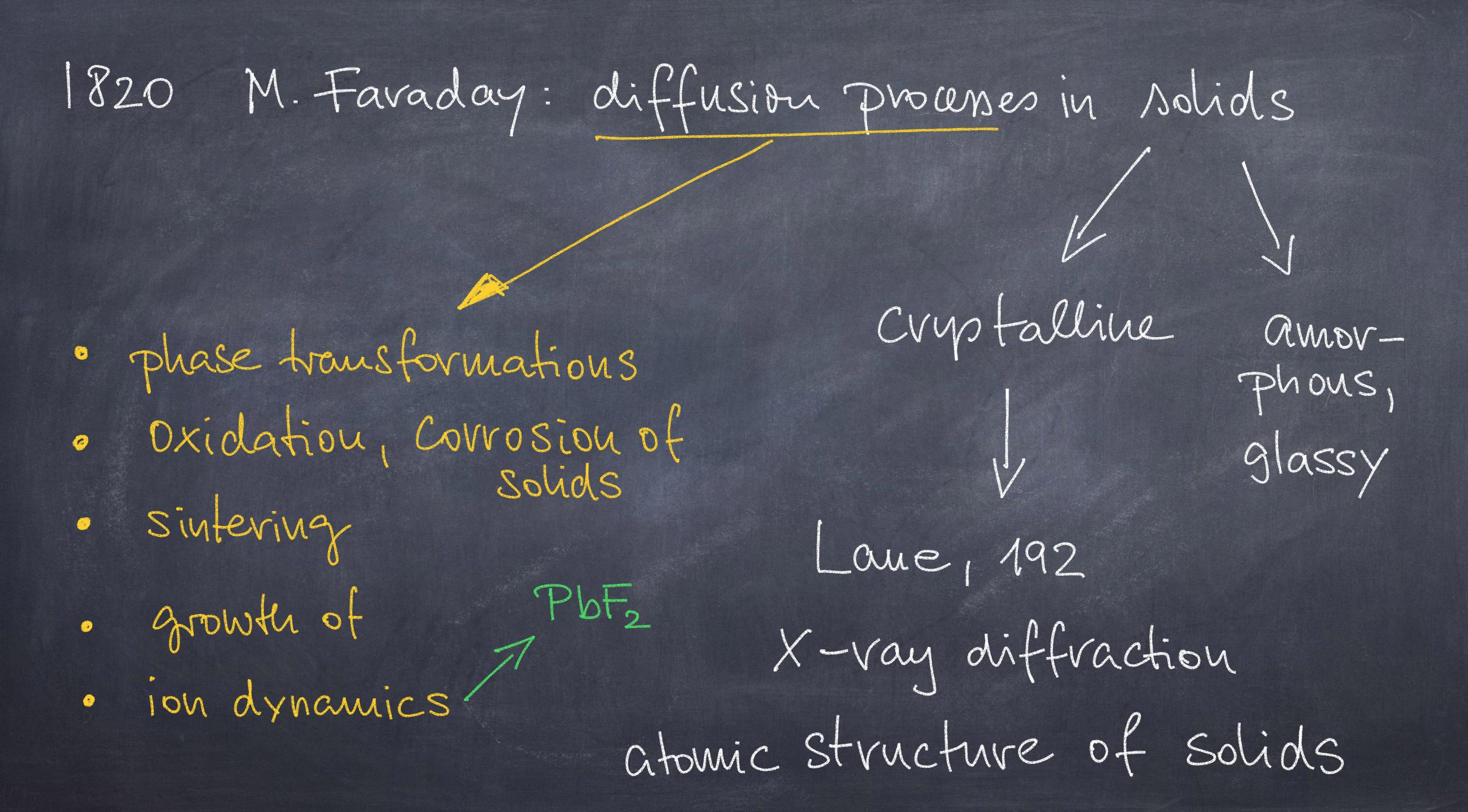
Ion Migration in Solids (Models, Methods, Materials)

Solid State Ionics 2024, LONDON

Some remarks: #+, Li+, Na+, F-, 02migration vs diffusion (hopping) Ion Migration in Solids crystalline (Models, Methods, Materials) amorphous polymers Solid State Ionics 2024, LONDON hopping concepts non-huclear vs huclear microscopic vs macroscopic

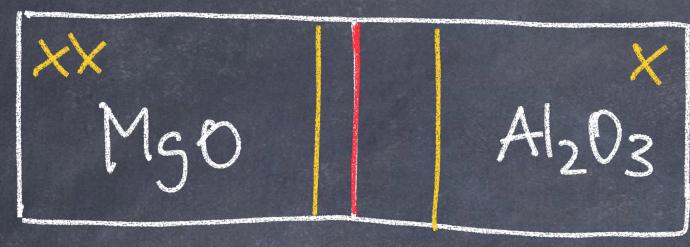


Example: separation line new brass phase Zu, Cu enviched in Cu, Zn depleted T=800°C, 120 min (kinetics)

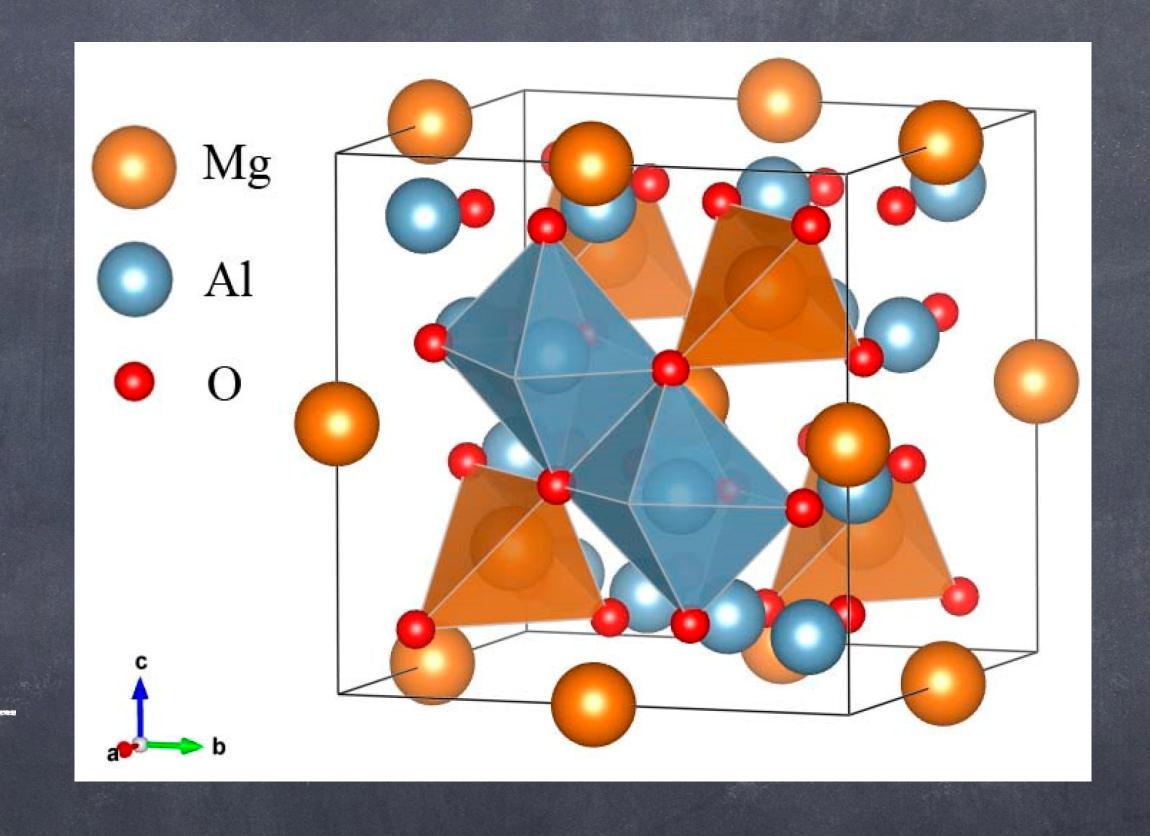
Example:

Formation of the MgA1204 Spinell

MgA1204



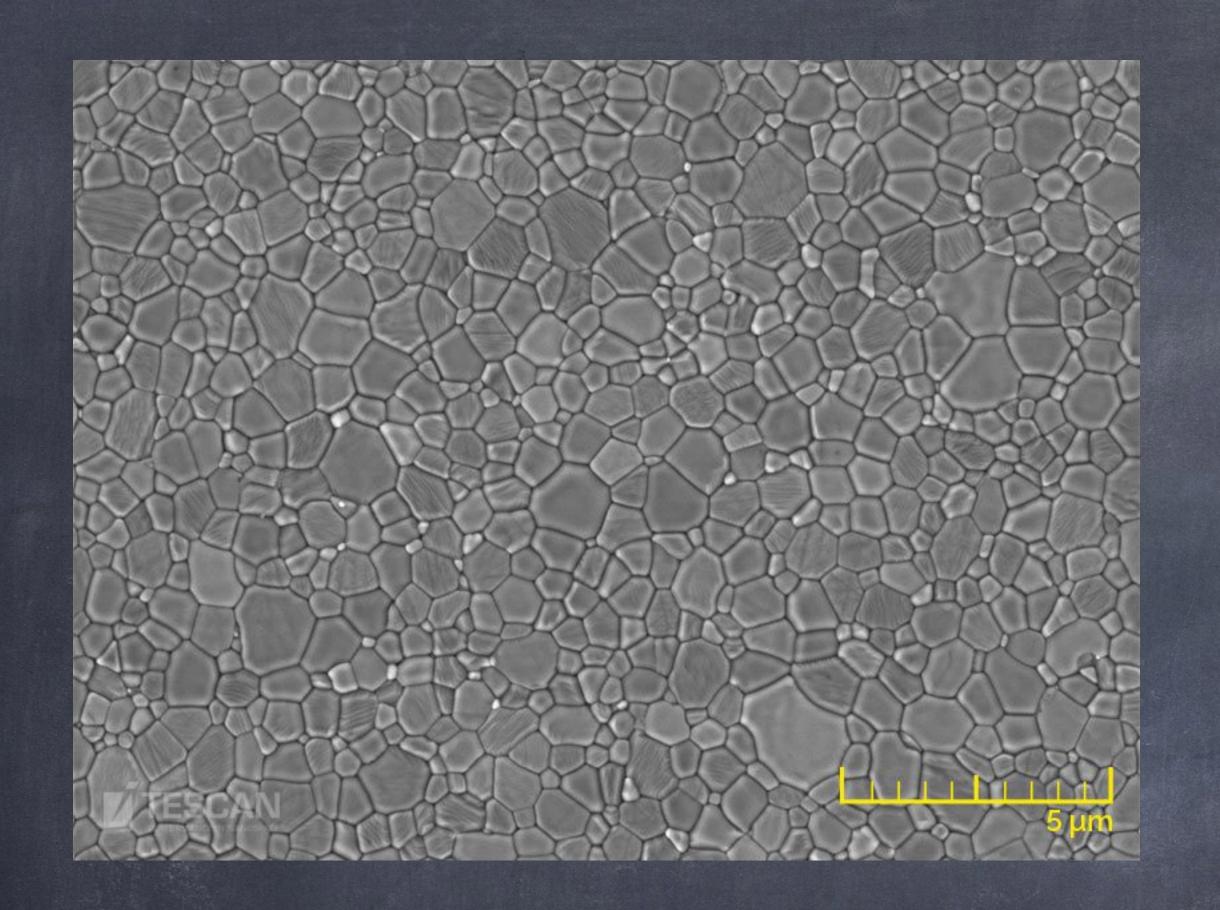
Mo2+ 2 of all tetrahedral sites occupied



padraging × hexagonal

XX Cerbic

A13+ 1 of the octahedral sites occupied



a Sintered ceranic

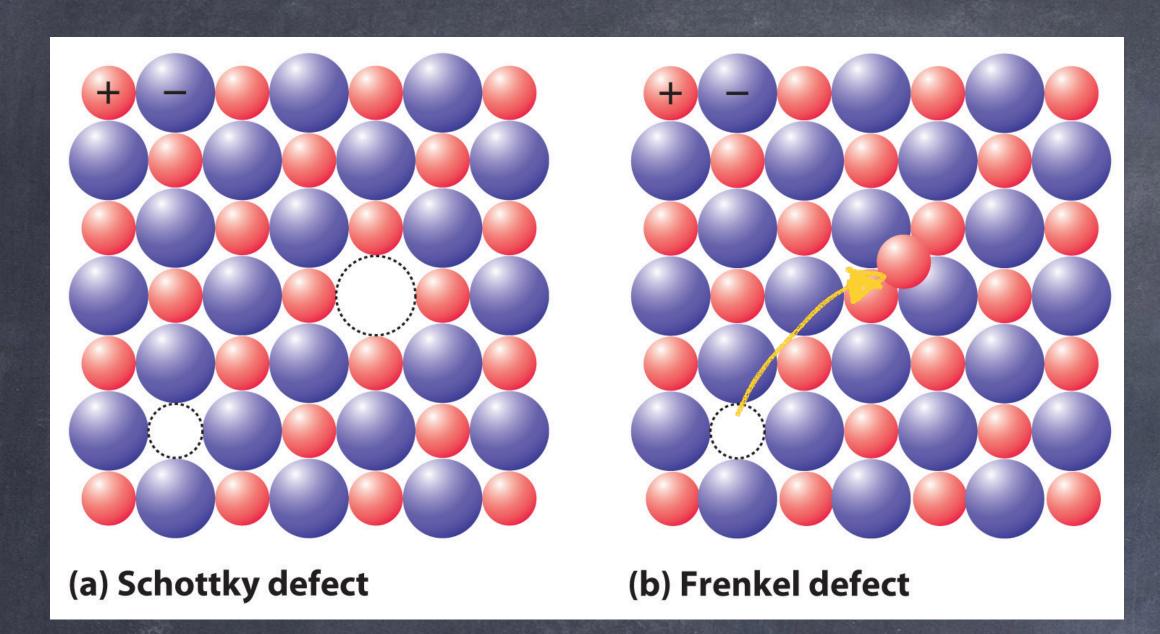
- · polycryptalline
- o grains and
- grain boundaires

Sintering at brigh temperatures:

and pressures

Mg0 (T > 1700°C)

Jource Conduction Harough



Mgo

AGI, AGCL
AGBY, CaF2
BaF2

defects

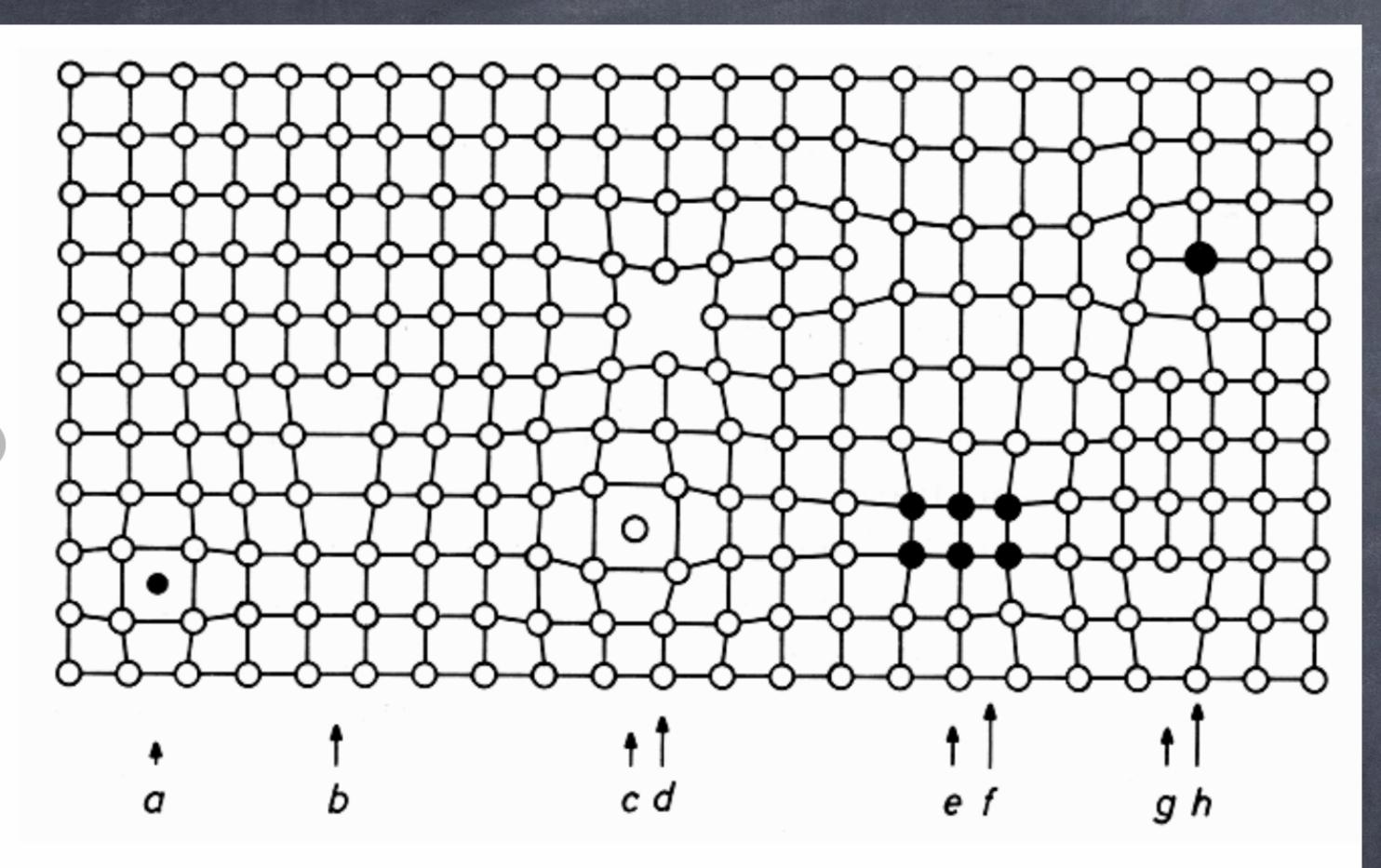
(: Vacaucy

interstitial site

AgCl: Ast on interstitial cation Frenkel defect Site

CaF2: F- on interstitial anion Frenkel defect site

more types of defects:



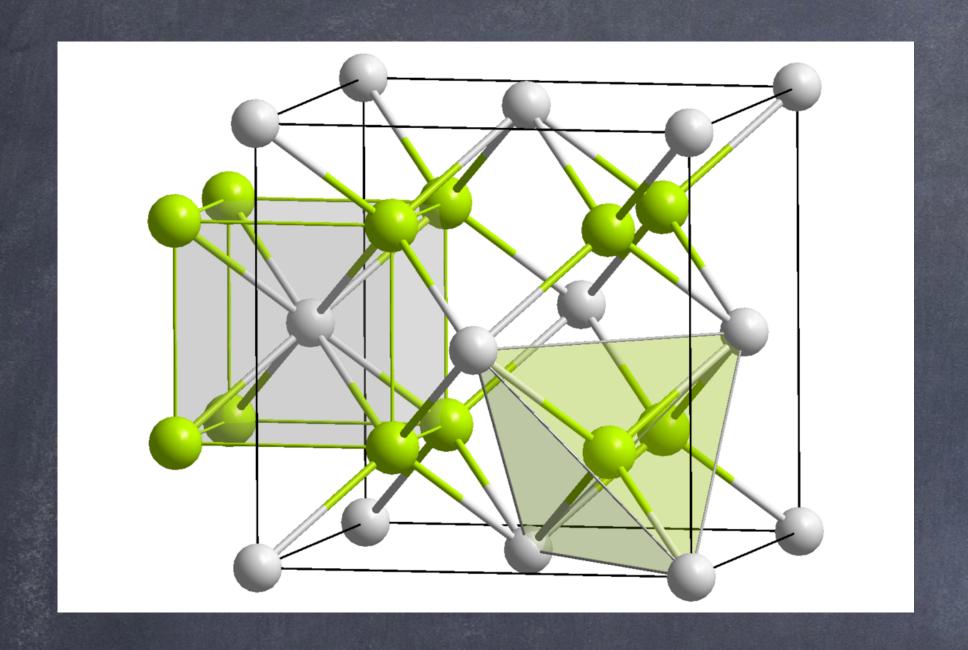
5 Types of crystal defects and impurities:-a) Interstitial impurity atom, b) Edge dislocation, c) Self interstitial atom, d) Vacancy, e) Precipitate of impurity atoms, f) Vacancy type dislocation loop, g) Interstitial type dislocation loop, h) Substitution impurity atom 2

look at the owrangements of the ions next to a defect!

5 types

Tdependence formation of dufects: * dominated by - TAS Gibbs / AH Tree LOWT energy at low [defect] the (enthalpie) influence of -TAS is relatively large! TAS [defect] defect concentration

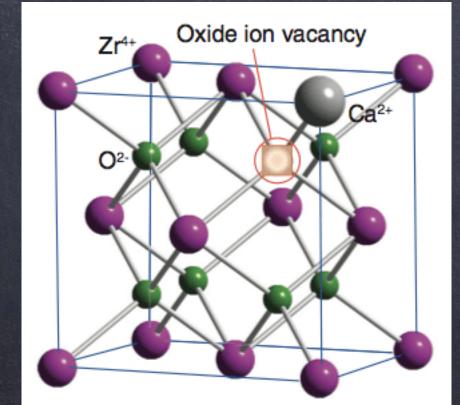
Cat₂

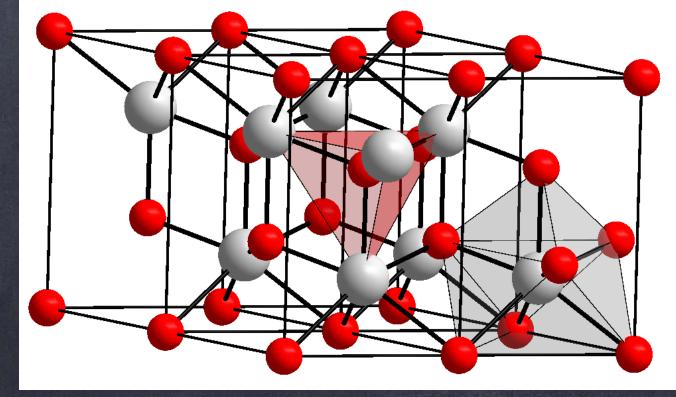


anions on tetrahedral sites (Small volume)

empty octahedral sites

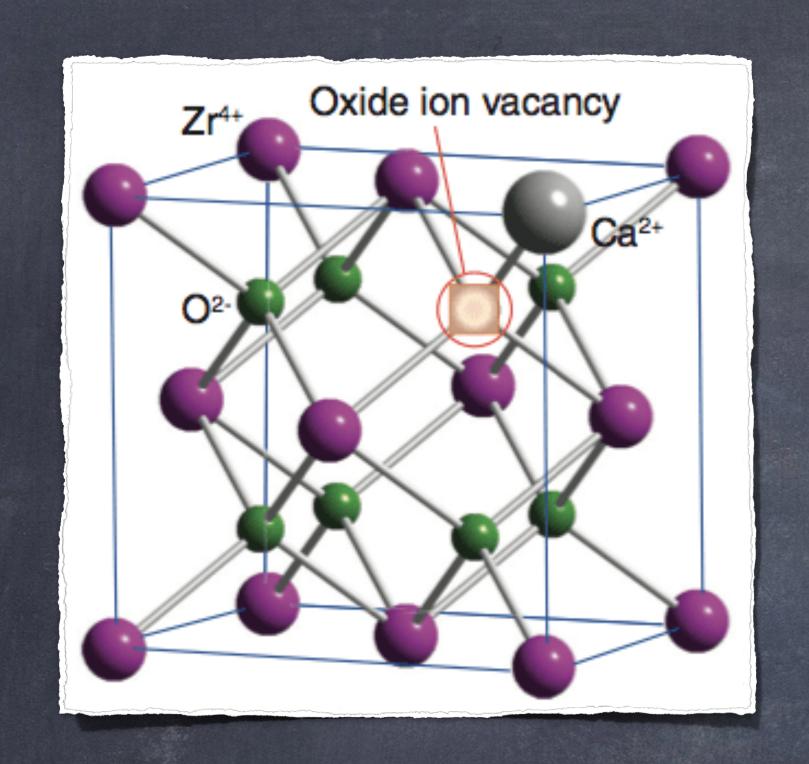
See also CeO2, ZrO2, Thoo





CeO2

Z102



Zv4+ is replaced with Co2+:

to ensure charge neutrality, an
oxygen vacamicy is formed.

02-uses this vacamey for diffusion!

What happens if you replace 2 Zr4+ with 2 Y3+ ions?

$$Y_{2}O_{3} \xrightarrow{\frac{14}{2}} 2Y_{2v}^{1} + 30_{o}^{\times} + V_{o}^{*}$$

$$[V_{o}^{*}] = \frac{1}{2} [Y_{2v}^{1}] \qquad \uparrow$$

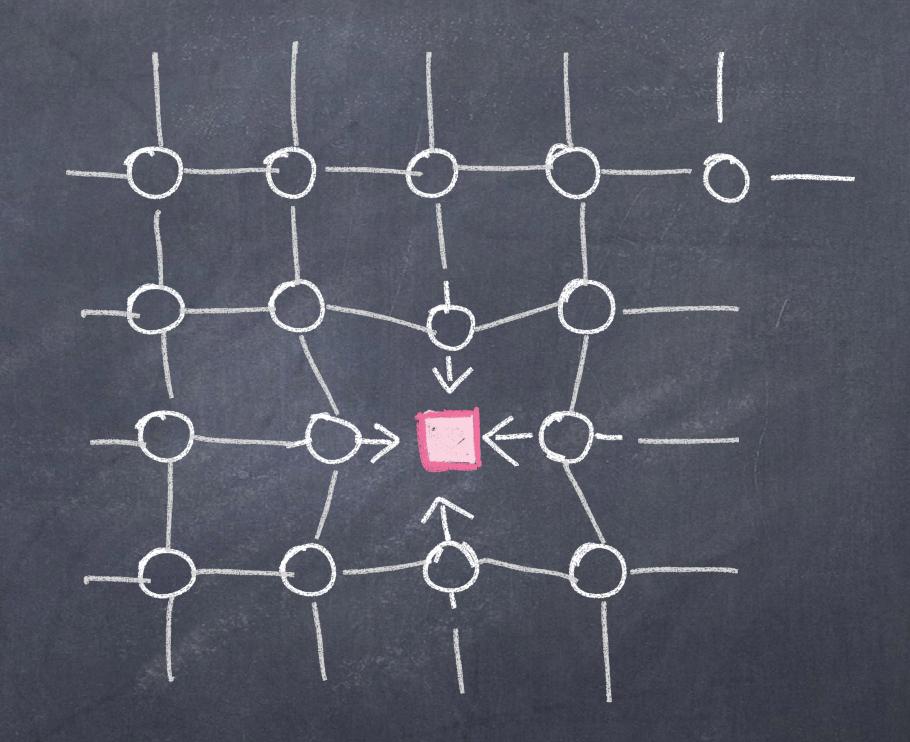
$$CaO \xrightarrow{\frac{14}{2}} Ca_{2v}^{1} + V_{o}^{*} + O_{o}^{\times} \qquad formation of O vacancies$$

Kröger-Vink motation!

Jumping of ions

... remember your lessons on themodynamics

$$0 \ 0 \ 0 \ 0 \ S = \frac{1}{28} \cdot \ln \Omega$$
 $0 \ 0 \ 0 \ 0 \ \Omega = 1$
 $0 \ 0 \ 0 \ 0 \ 0$



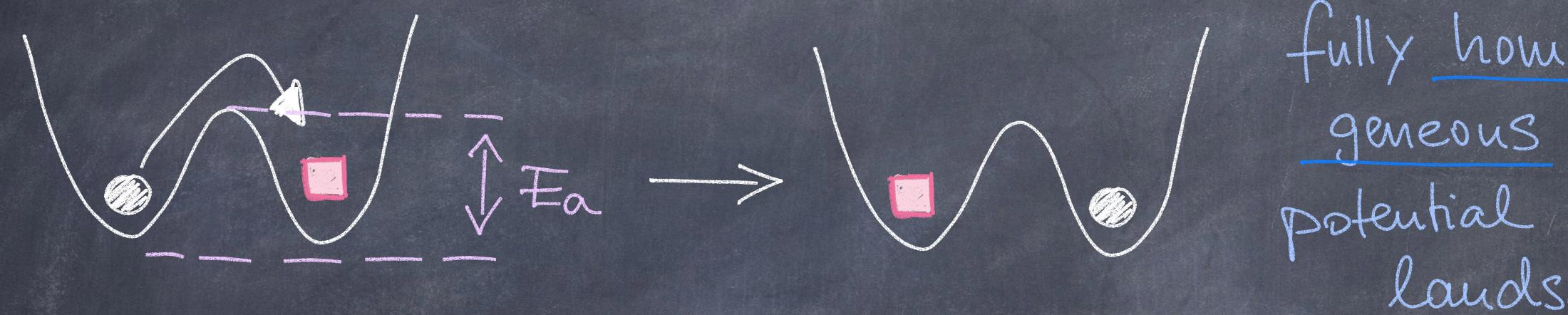
perfect crystall

TIDK



: Vacaut Site

What happens on the Angström length scale?



tully homolandscape

Ea: activation energy

$$\tau^{-1} = \tau_0^{-1} \exp\left(-\frac{E_0}{R_B \tau}\right)$$

7: jump vate

Potential potential landscapes S: Symmetric a: asymmetric Ea S regular regular / transition states oct.-tetr.- oct. (LixTiS2) irregular (glasses) - Short range vs. Long range

just introduce some asymetry Funke, Minustes, Germany

> localised motion, no long-range ion transport

RELAXATION VS. BACKWARD JUMP(S) a concept

fast lattice relaxation

ion transport/ migration jumps and velaxation

local jumps

activation barner 0.5 eV moderate ion conductor

relaxtion of latice

0. -> 2: Successful jump

backward

no back-Ward jump

number et jumps per second: Ealactivation < 0.5 eV energy 109 s-1 extremely fast 106 s-1 fast 0.5 eV 104 s-1 Slow to moderate > 0.5 eV ... 1.0 eV < 104 5-1 poor conductor or lingher 1 = 1 e - Ea/(kB.T) jump rate 1 pre-factor contains attempt quency attempt frequency: 1014 s-1 (phonon frequencies) - Fa/ReB = 1 = 1 = - KBT fast conductor $\sim ln \frac{1}{T} \propto -\frac{Ea}{RB} \cdot \frac{1}{T}$ slow conductor · change Ea or

· manipulate 1

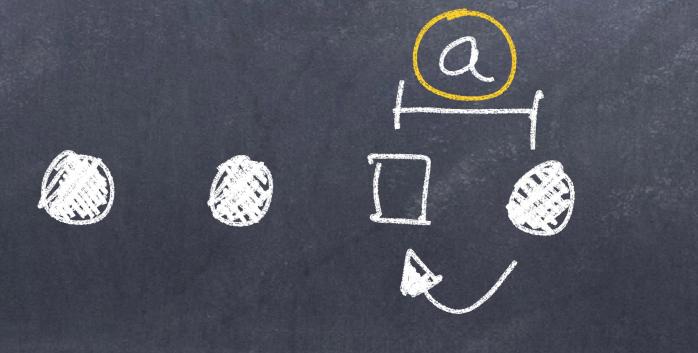
attempt frequency: 1014 s -1 (phonon frequencies) $\frac{1}{t} = \frac{1}{t_0} e^{-\frac{t_0}{K_BT}}$ fast conductor -1 $ln \frac{1}{7} \propto -\frac{Ea}{RB} \cdot \frac{1}{T}$ slow conductor very Low Ea,
very Low 1/20 (Meyer-Neldel)

· change Ea or

· Manipulate 1

$$Dsd = \frac{a^2}{2d \cdot \tau}$$

$$\mathcal{D}_{sd}^{sd} = \frac{a^2}{6.7}$$



an approximation

D can be converted into a conductivity 3

$$D = \frac{3kBT}{N9^2}$$

Solid state diffusion coefficient based on the

NERNST-EINSTEIN

equation

N: no. of charge carriers/ Volume

9: charge of the mobile Species

F-, Lit, Agt,
Mg2+

T: Tracer

$$D_{T} = D_{0} e^{-\frac{E_{0}}{k_{B}T}}$$

$$D_{T} = H_{R}D = H_{R} \frac{3 \cdot k_{B}T}{N \cdot q^{2}}$$

$$\frac{1}{2} D_{T} = f$$

$$D sd = \frac{a^2}{2d\tau}$$

$$f$$
: correlation factor $(0 \le f \le 1)$
 H_R : Haven ratio

taken together:

$$D_{\text{tracer}} = H_r \frac{\sigma k_B T}{Nq^2} = fa^2/(6\tau)$$

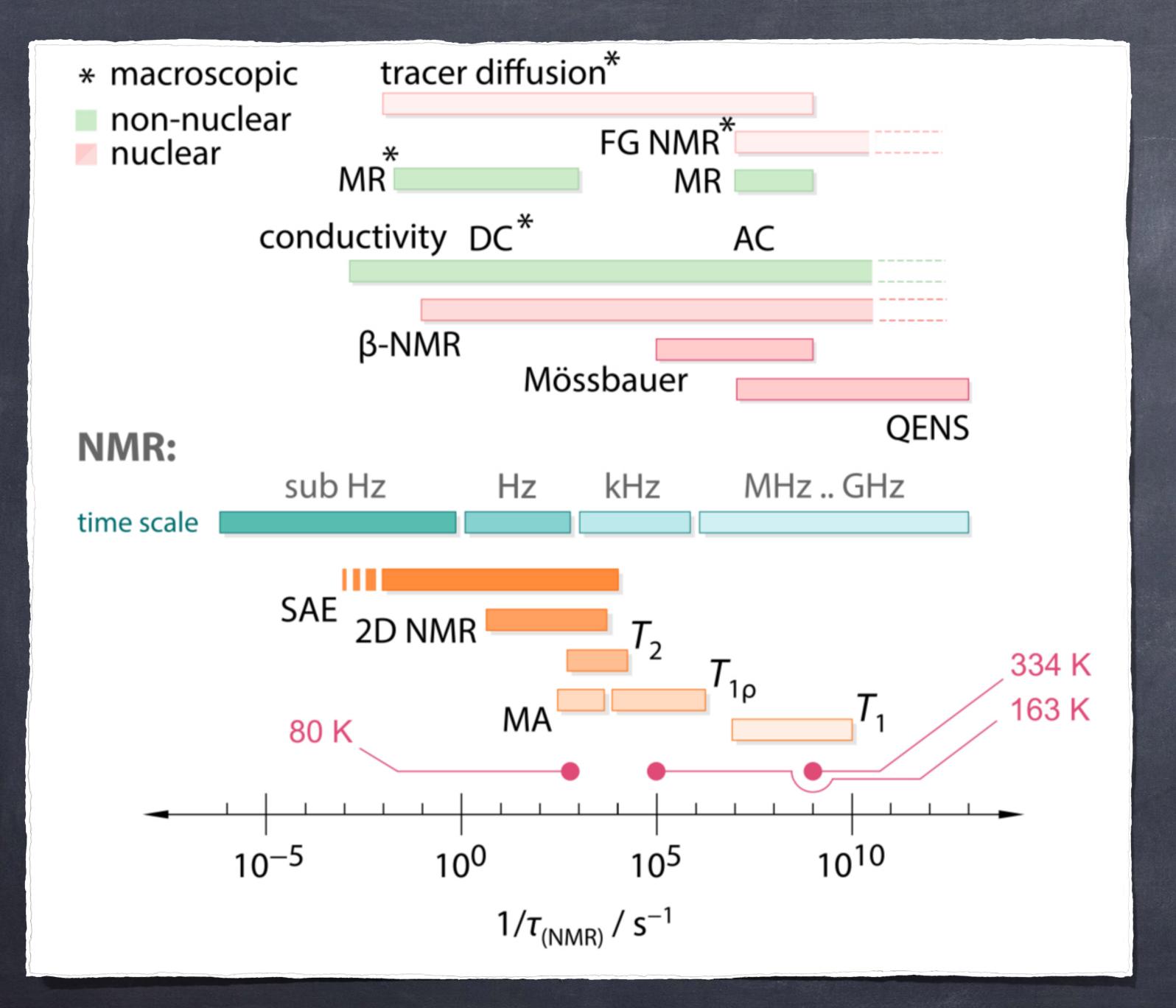
$$\tau^{-1} = (H_r/f) \frac{6k_B T}{Nq^2 a^2} \cdot \sigma$$

METHODS:

How to measure

Dor T-1 2

- · simple diffusion mechanism
- · uncorrelated (random) jump diffusion



FG: field gradient (NMR) MR: mechanical relaxation

William Vm

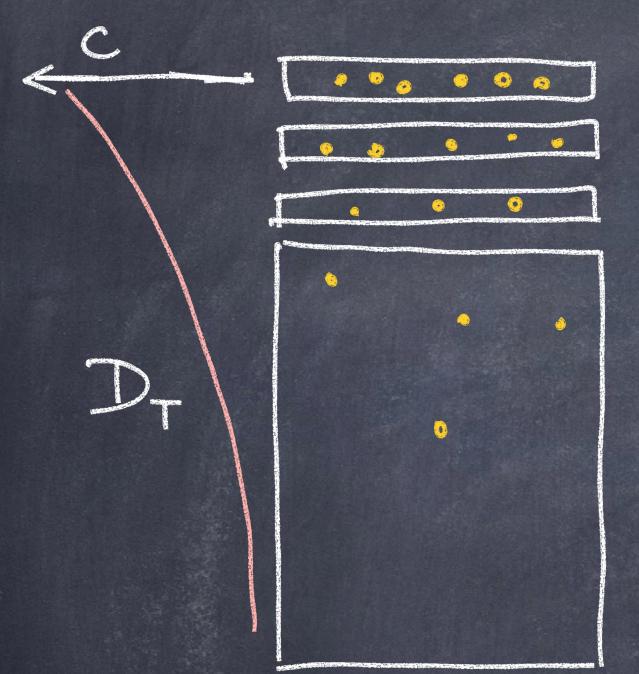
QENS: quasi elastic neutron Scattering

T1,2,8: relaxation NMR

MA: motional averaging

SAE: Spin-alignment NMR TRACER

NMR

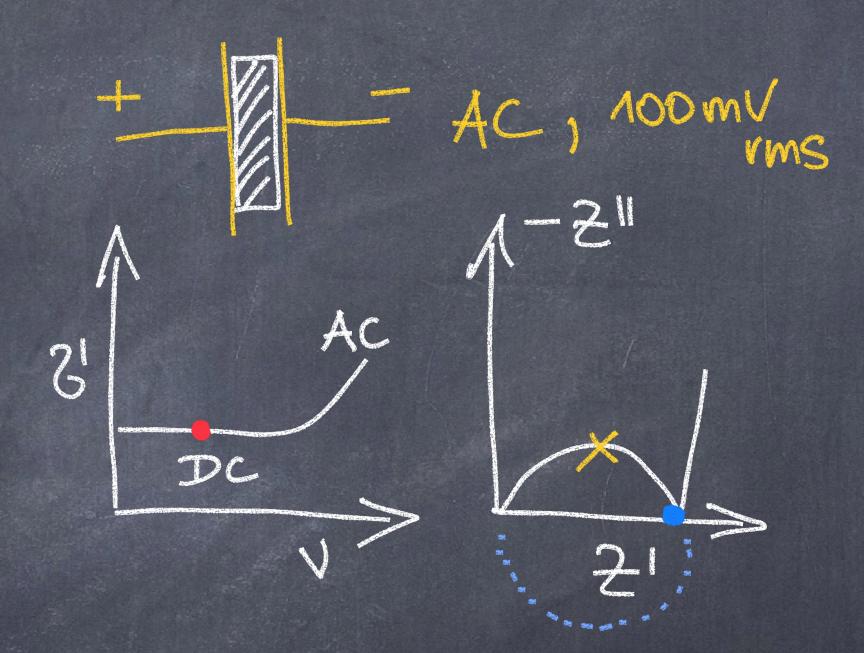


ΔE=ħwo radio tracer

- measure concentration profile
- · measure relaxation vates

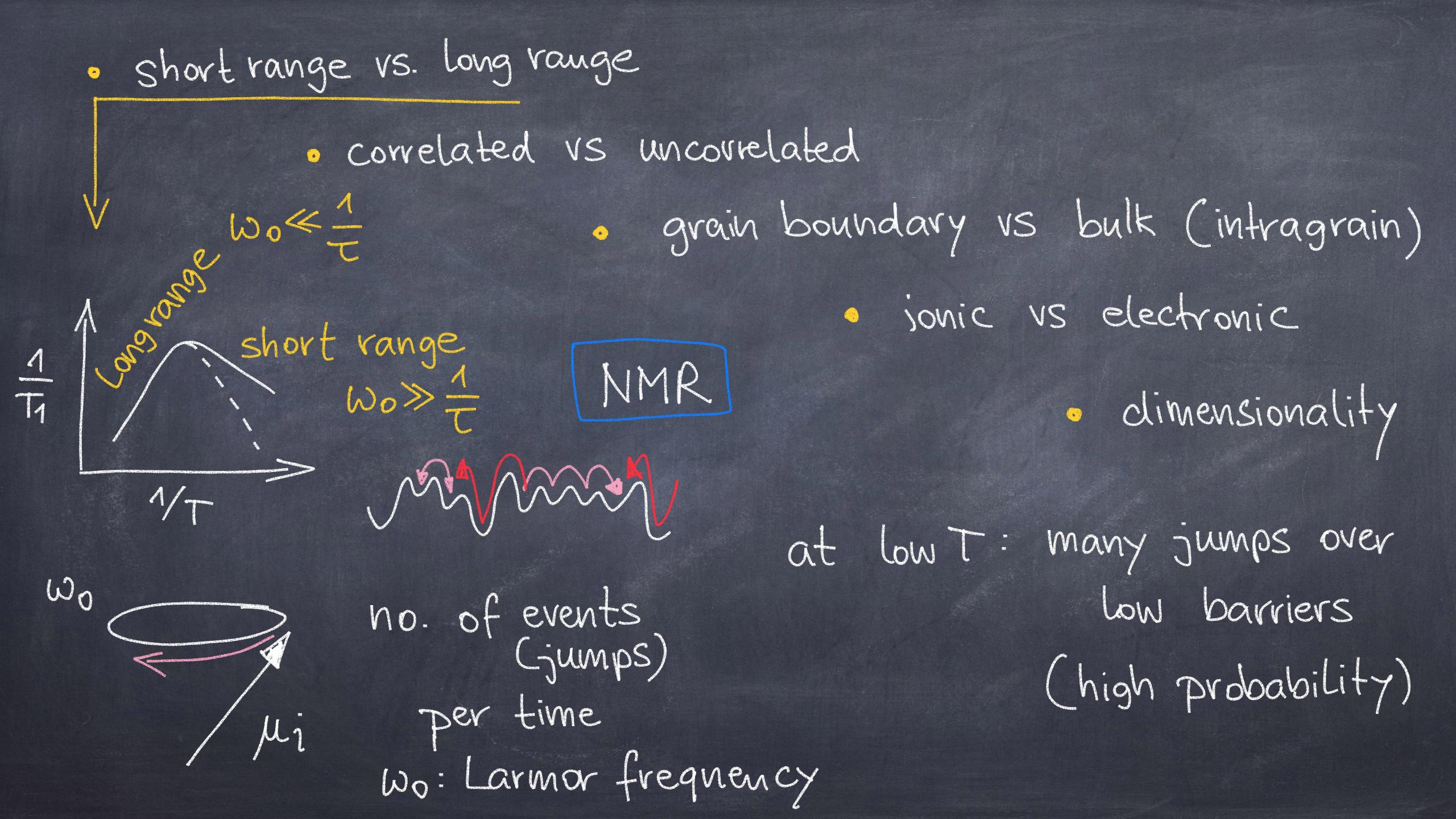
X: Tcwo 21

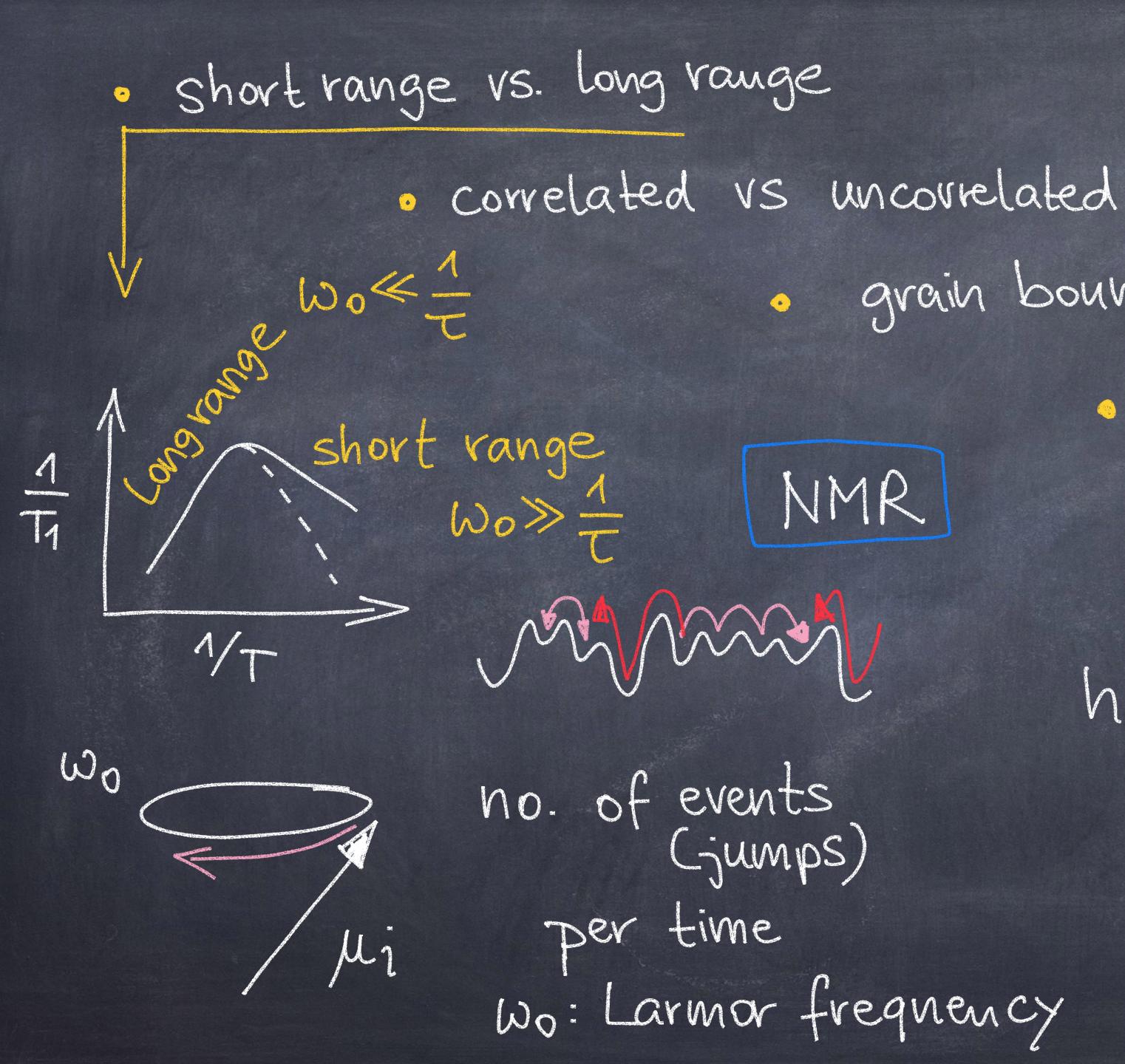
CONDUCTIVITY ACIDC



- conductivit
- impedancé

X: WeCR 21





grain boundary vs bulk (intragrain)

jonic vs electronic

NMR

climensionality

high T: probability to

detect jumps

over high barriers

increases

- · Short range vs. Long range
 - · correlated vs uncorrelated
 - · grain boundary vs bulk (intragrain)

successful jumps

o jonic vs electronic

3DC = f(T) 3AC = f(T)

· dimensionality

DC V

Frequency

dispersive region
forward, backward jumps
localised motions,

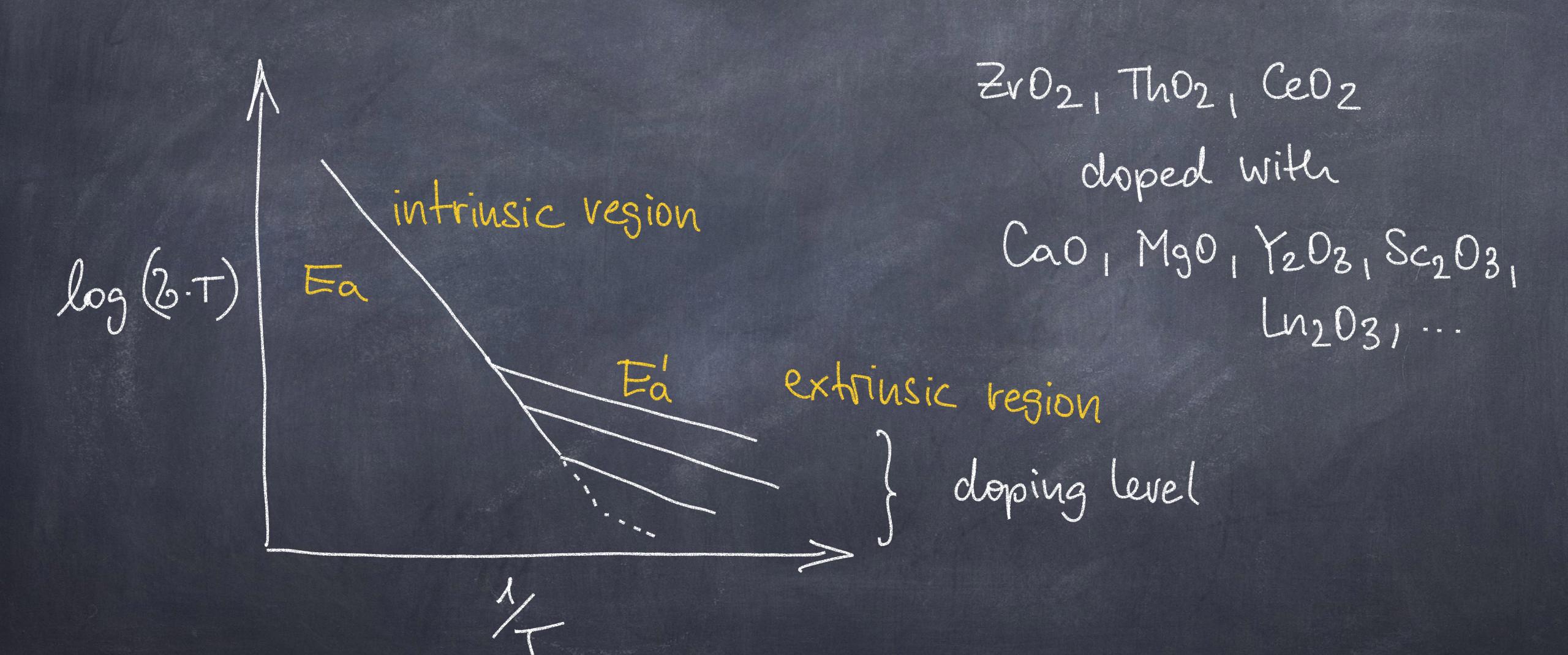
NCL behaviour at Low T

· Short range vs. Long range · correlated vs uncorrelated grain boundary vs bulk (intragrain) jonic vs electronic CONDUCTIVITY NMR dimensionality 65 BT uncorrelated

· Short range vs. Long range · correlated vs uncorrelated grain boundary vs bulk (intragrain) o jonic vs electronic CONDUCTIVITY NMR dimensionality uncorrelated

conductivity can also directly be measured: impedance Spectroscopy Ea = 2. Ea (in some cases) intriusic vesion $2 = \frac{20}{4} e^{-\frac{1}{2}} (KBT)$ log (2.T) E plot ln (3.T) vs 1 extrinsic region 609 (B.T) VS 1

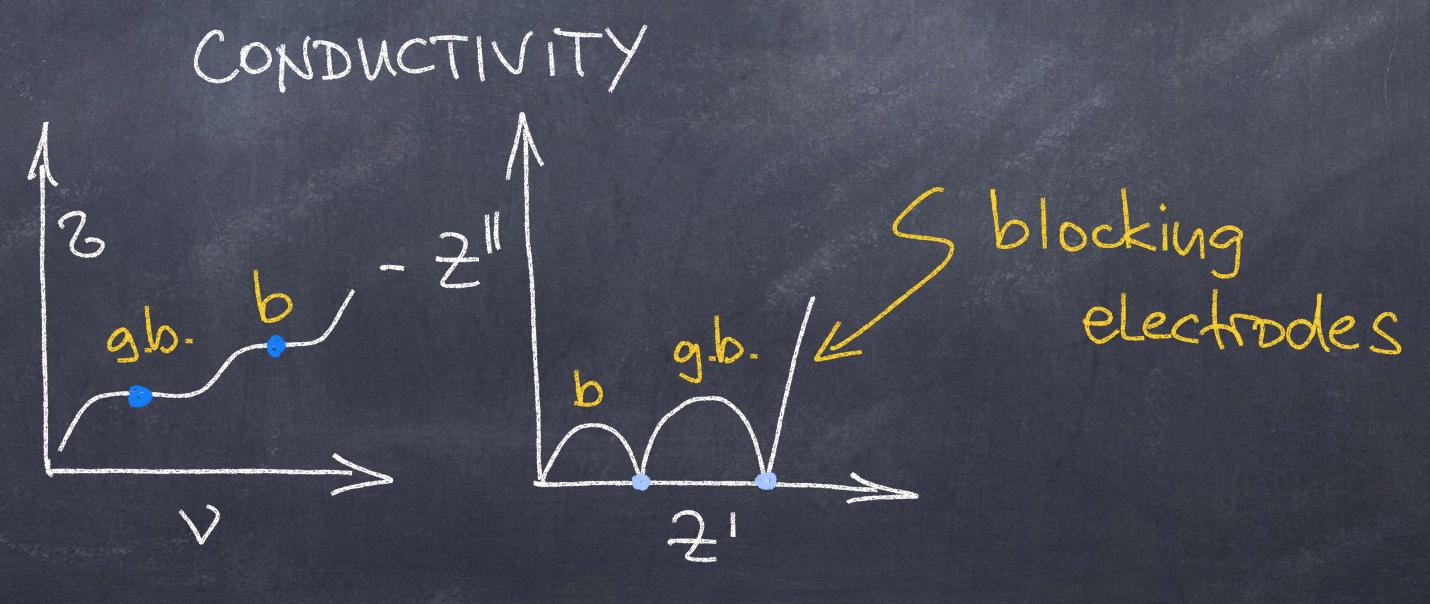
... polyantalline Samples and Single crystals:



- · Short range vs. Long range
 - · correlated vs uncorrelated
 - grain boundary vs bulk (intragrain)
 - o jonic vs electronic
 - · dimensionality

NMR
needs many spins
in 9.6.
regions

· nanocrystalline materials



- · Short range vs. Long range
 - · correlated vs uncorrelated
 - · grain boundary vs bulk (intragrain)
 - o jonic vs electronic

NMR (74, 23Na, 1H)...)
is sensitive to ionic dynamics

Conductivity: Beau < Brotal

Chronoamperometric meas. (polarisation) M= coust.

M= coust.

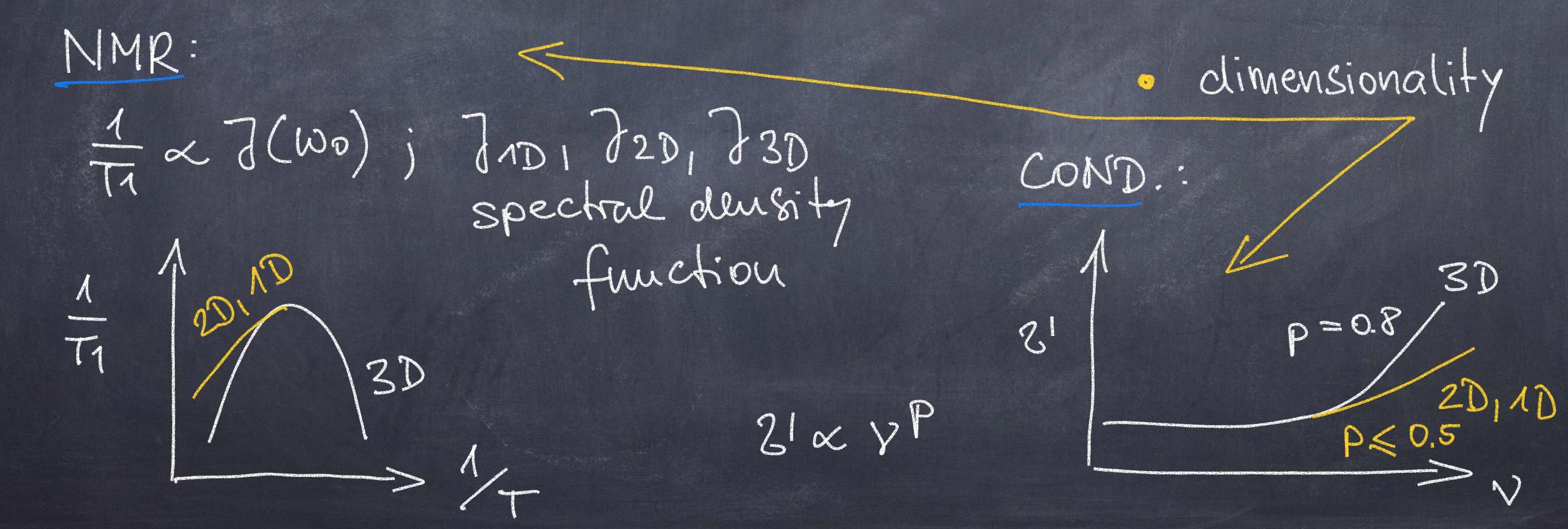
Beon

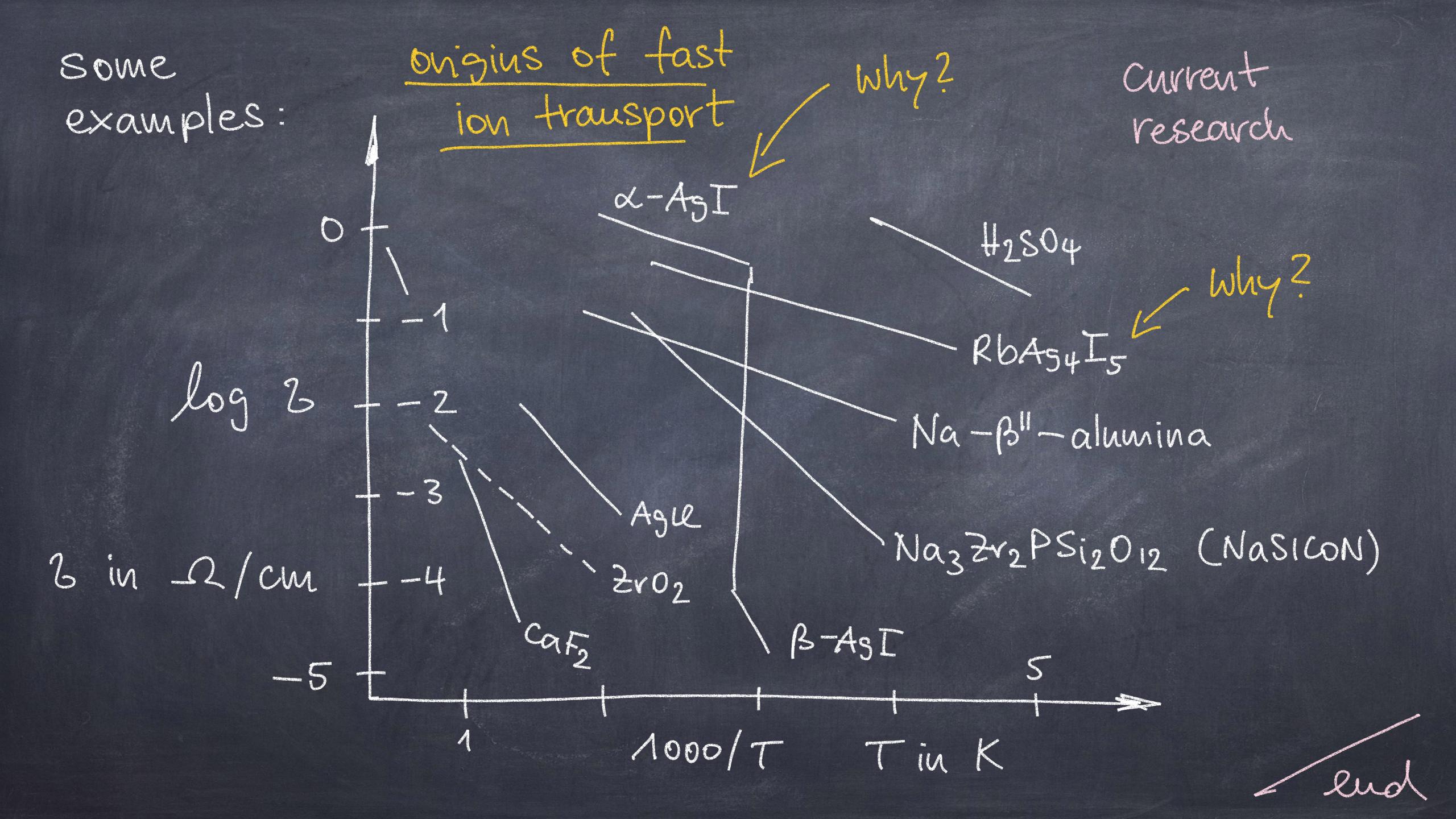
Inot

t

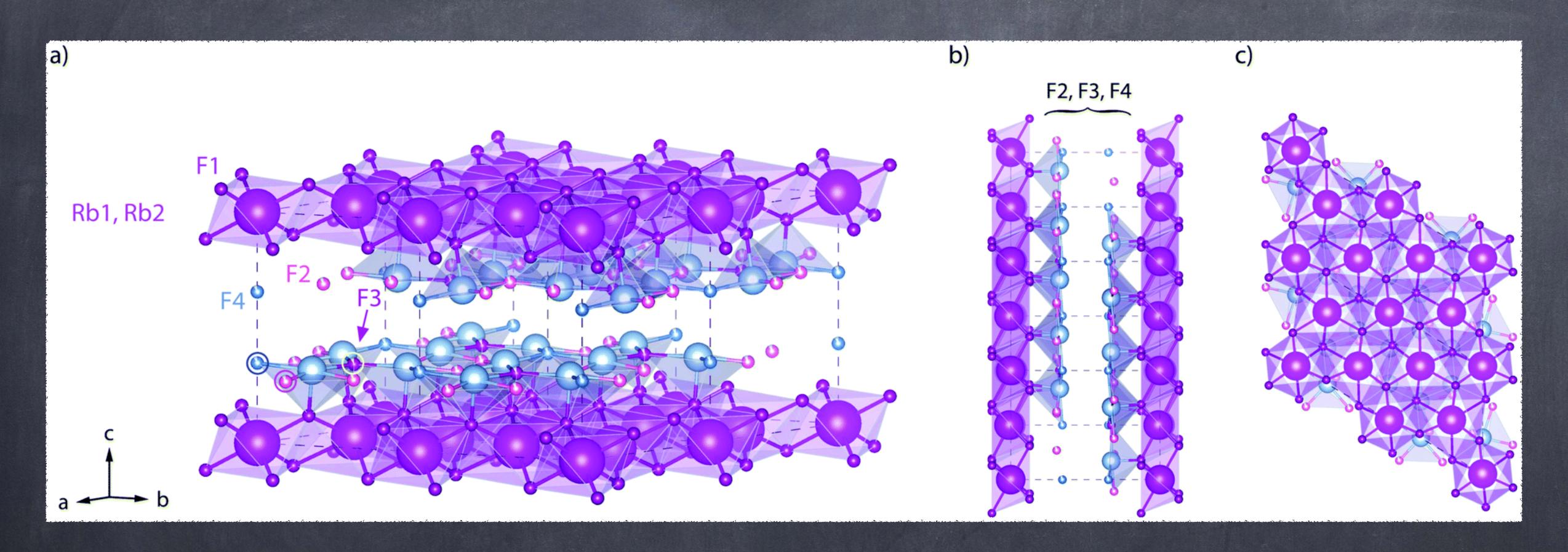
· climensionality

- · Short range vs. Long range
 - · correlated vs uncorrelated
 - · grain boundary vs bulk (intragrain)
 - o jonic vs electronic



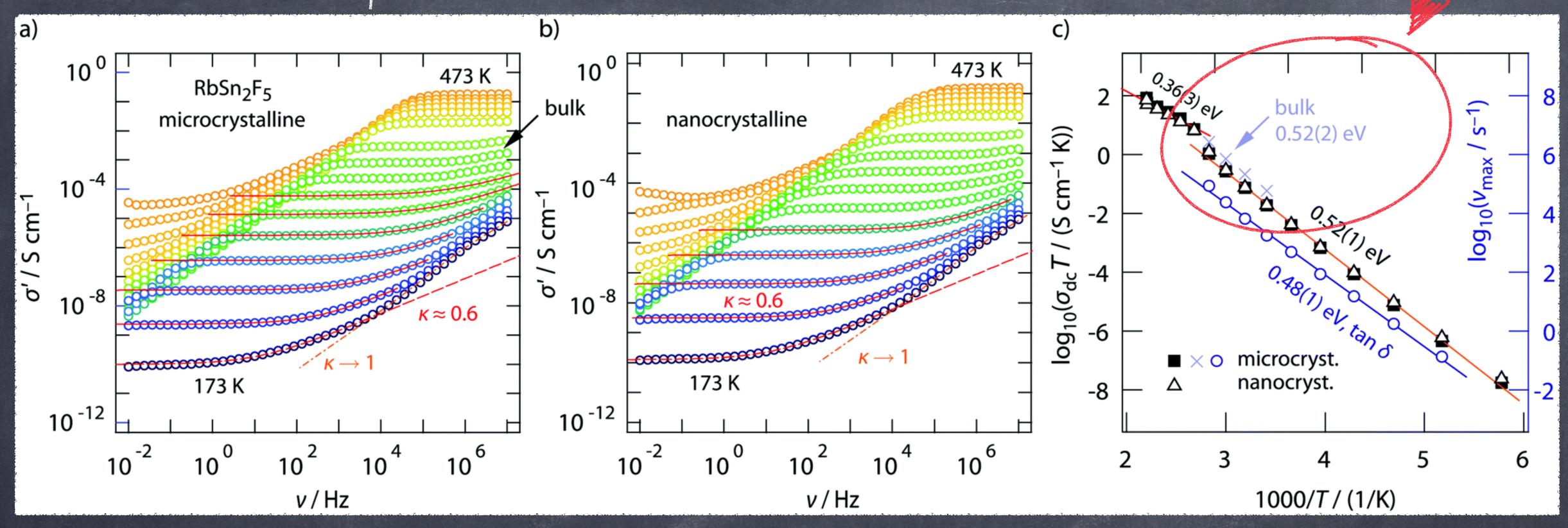


... a final example: RbSuzF5 (just few images)



a 2D ionic conductor?

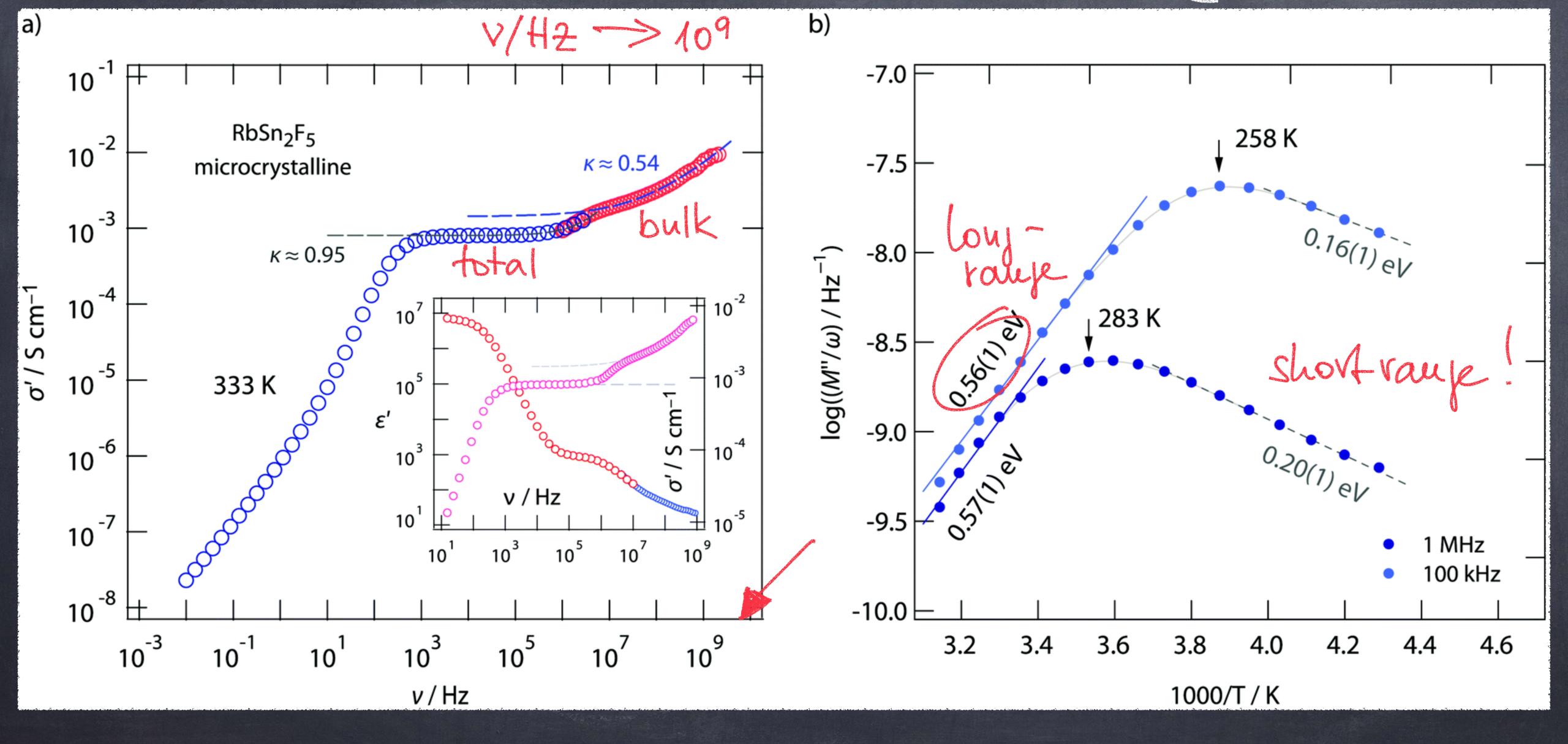
Conductivity isotherms:



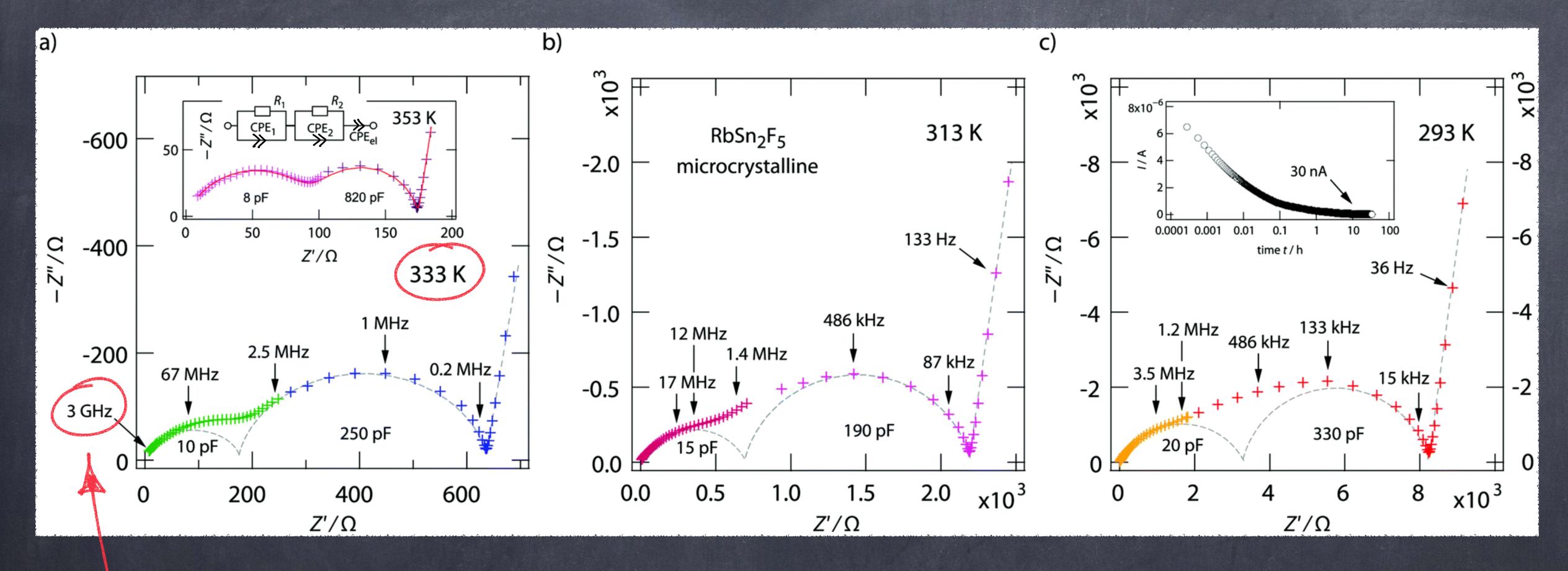
activation energy: ~ 0.48 eV. 0.52 eV (F-)

bulk vs. 9.6./Hotal

M" & = : bulle!

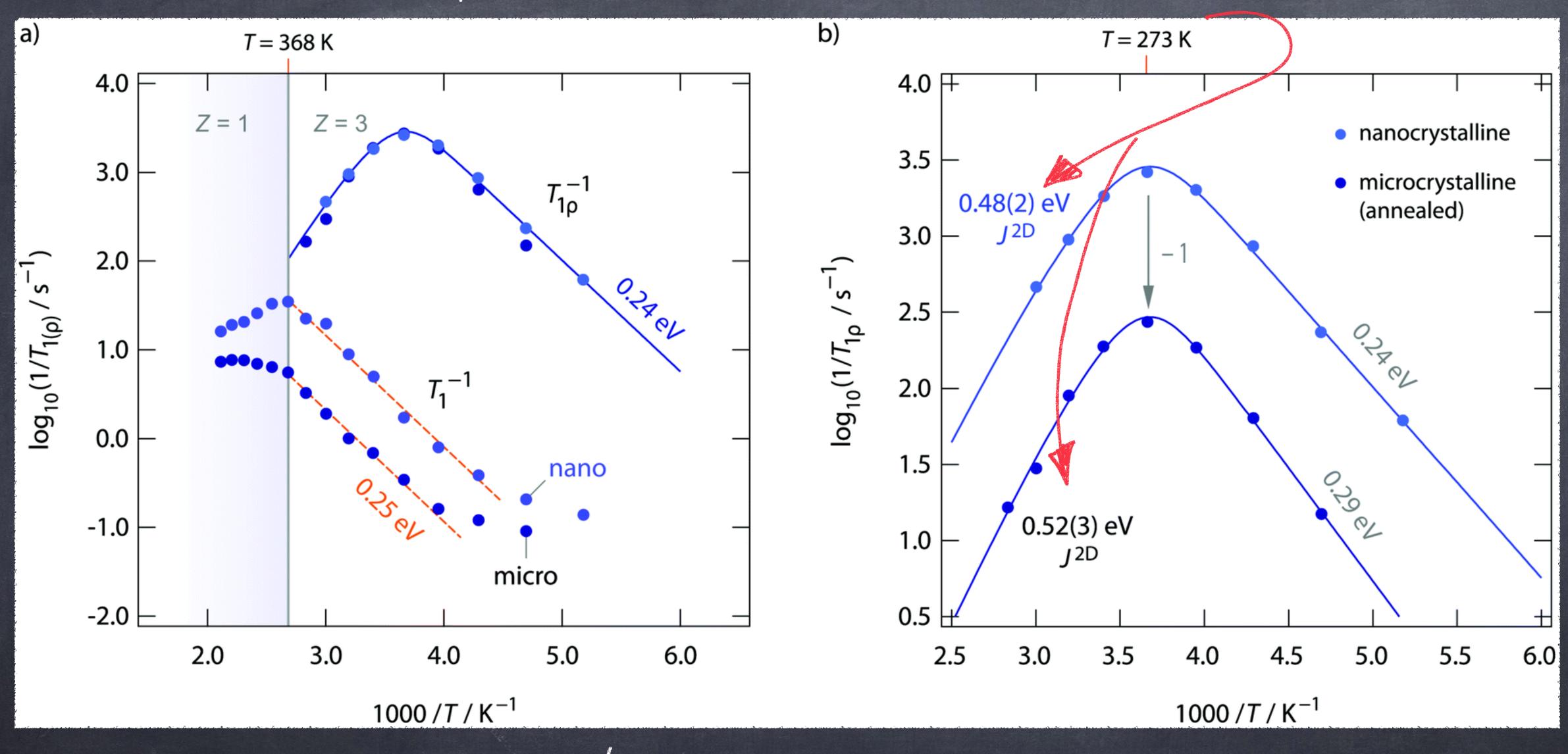


Nyquist phots:



3 8Hz! apex: 67 MH2

NMR: 2D spectral density function J2D (---)



(3) Consistent result! Ea, T, D

Thale you!

all the best!